

B4

13. (Twice Amended) A semiconductor device which has an insulating nitride layer formed as a buffer layer from a group III-V nitride compound semiconductor heavily doped mostly with cadmium.

B5

16. (Amended) A semiconductor device as defined in Claim 13, in which the insulating nitride layer is heavily doped substantially with said cadmium as an impurity.

B6

18. (Amended) A semiconductor device as defined in Claim 13, in which the insulating nitride layer is doped with said cadmium in an amount not less than $1 \times 10^{17}/\text{cm}^3$.

✓
Please cancel claims 3 and 17.

REMARKS

Claims 1-27 are pending in the application. Claims 6-12 and 20-27 are withdrawn from consideration as being directed to a non-elected invention. In the Final Office Action of November 5, 2002, the Examiner made the following disposition:

- A.) Required corrected drawings.
 - B.) Rejected claims 2-4 and 16-18 under 35 U.S.C. §112, second paragraph.
 - C.) Rejected claims 1-5 and 13-19 under 35 U.S.C. §102(e) as being anticipated by *Shakuda*.
- Applicants respectfully traverse the rejections and address the Examiner's disposition as follows:

A.) Requirement for corrected drawings:

As per the Examiner's request, Applicants herewith submit corrected Figures 12, 13, and 14.

Applicants respectfully submit that the requirement has been met and request that it be withdrawn.